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(54) Title: SOLUTION PREPARATION APPARATUS AND METHOD FOR TREATING INDIVIDUAL SEMICONDUCTOR WORKPIECE

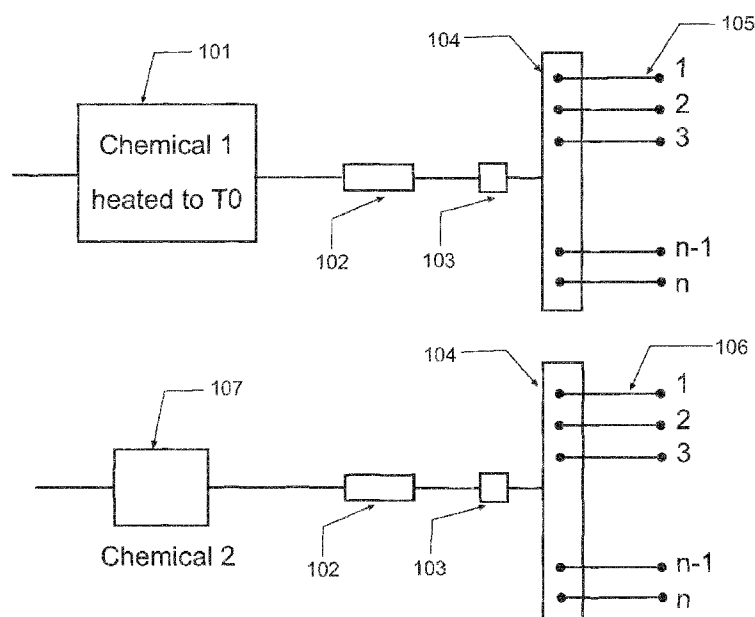


Fig. 1

(57) Abstract: A low-cost apparatus for chemical solution preparation with controlled process parameters is provided. Such parameters include chemical age, temperature, yield of active ingredients at the point of use, and so on. In addition, the apparatus provides chamber-to-chamber consistency on these parameters across multiple processing chambers in a single wafer wet-clean system. A method utilizing resident time of the chemical solution mixture to achieve optimal combined effect of the chemical solution mixture for best wafer treatment results is also provided.



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